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THREE-DIMENSIONAL NANOBIOCOMPUTING ARCHITECTURES WITH NEURONAL HYPERCELLS

Microsystems & Nanotechnologies

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14. ABSTRACT <i>Microsystems and Nanotechnologia</i> performance computing and processin design technology is based on utilizi module-system) within enabling orga - computer-aided-design (CAD) tool technology. The technology departs f and CMOS fabrication. Novel solu processing) were utilized using de implement designed ^M ICs as molecu developed and demonstrated. The de- and applied research were integrated v tools and proof-of-concept software.	<i>es</i> investigated a novel 3D ³ (Hardward ng platforms utilizing molecular hardw ing a three-fold solution: (1) Innovativ nization/architecture solutions utilizing s supported by new synthesis and desi from conventional planar ICs design (V utions of massive parallel distributed vised 3D hypercubes (data structure lar electronics hardware. Novel highly sign was accomplished utilizing linear vithin innovative computing and molecu	e-Software-Nanot are within a /e hardware g molecular gn methods: /LSI, ULSI computing assemblies r-efficient sy decision dia lar electronic	^{echnology)} technology to design super-high- n enabling organization and architecture. The - 3D-topology molecular hardware (device- integrated circuits (^M ICs); (2) Novel software ; (3) Nanotechnology - molecular fabrication and post ULSI), von Neumann architectures, and processing (pipelined due to systolic) and neuronal hypercells ([®] hypercells) to ynthesis taxonomy and design concepts were grams and linear systolic arrays. Fundamental cs technologies developing representative CAD		

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The <u>overall objective</u> was to start the development of a novel $3D^3$ (Hardware-Software-Nanotechnology) technology for super-high-performance three-dimensional (3D) molecular/biomolecular computing and processing platforms to accomplish demanding mission-specific computing to support Air Force tasks.

The **specific objectives** were:

- 1. Utilizing a unified bottom-up/top-down synthesis taxonomy, design super-high-performance computing (processing) platforms implemented using molecular integrated circuits (^MICs). Devise innovative organizations/architectures and assess 3D³ technology researching novel hardware, software, design methods and molecular electronics (nanotechnology) solutions.
- 2. Develop and demonstrate logic design methods in synthesis of 3D^MICs for computing platforms. Perform the 3D-centered design of super-complex combinational circuits by using hypercubes as homogeneous aggregated data structure assemblies. Assess the technology-centric Super Large Scale Integration (SLSI), and analyze the implementation of ^MICs utilizing neuronal hypercells (⁸hypercells) as the molecular hardware primitives. Develop and apply performance indexes to evaluate molecular electronics and ^MICs.
- 3. Propose molecular electronic devices (^{ME}devices). For a multi-terminal ^{ME}device, perform modeling and analysis of electron transport to assess the applicability of ^{ME}devices for molecular gates (^Mgates), ^Nhypercells and ^MICs. Develop and demonstrate the fundamentals of CAD-supported synthesis, design, analysis and evaluation methods. Start the development of proof-of-concept CAD tools. The representative CAD software should perform illustrative design and analysis tasks at the device and system levels. Demonstrate the design for combinational circuits, including a 8- or 9-bit arithmetic logic unit (ALU).

For the **SOW Task 1**, *Microsystems and Nanotechnologies* developed and demonstrated a nanotechnology-centric synthesis taxonomy to design super-high-performance computing and processing platforms. We developed a unified bottom-up and top-down synthesis taxonomy to concurrently support $3D^3$ technology. This synthesis taxonomy was evaluated emphasizing different molecular (nanotechnology) hardware and processing paradigms.

For the **SOW Task 2**, *Microsystems and Nanotechnologies* developed and demonstrated a new computationally efficient method in the design of ^MICs. This technology-centric design results in the synthesis of complex ^MICs using hypercubes to represent data structures in 3D, and implementation of ^MICs by [®]hypercells. The proposed concept allows one to design and implement innovative organizations and architectures. The design is supported by developing proof-of-concept software supporting the $3D^3$ technology. The performance estimates were derived and estimated in order to obtain coherent indexes and metrics at the device and system levels.

For the **SOW Task 3**, *Microsystems and Nanotechnologies* examined the feasibility, soundness and baseline performance characteristics of prospective molecular and biomolecular devices which form molecular and biomolecular processing hardware. With emphasis on the foreseen synthesis technologies, fabrication feasibility, soundness and affordability, we proposed to utilize monocyclic organic molecules as multi-terminal *solid* ^{ME}devices to engineer ^Mgates which form ^Nhypercells and ^MICs. Electron transport in a *solid* ^{ME}device was examined to obtain baseline device characteristics and performance estimates. The representative proof-of-concept CAD tools in the logic design of ^MICs were developed and demonstrated for ALUs and other combinational circuits.

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SUMMARY

Under USAF contract, *Microsystems and Nanotechnologies* performed research and technology development in three-dimensional (3D) computing architectures. The major accomplishments were:

- 1. A unified bottom-up/top-down synthesis taxonomy was developed accomplishing a coherent design of an innovative computing platform implemented using Molecular Integrated Circuits (^MICs) within an enabling organization and architecture. Reconfigurable networking-and-processing was provided by a neuromorphological architecture, fused processing-and-memory organization, and molecular hardware. This project integrated novel hardware, software, design methods, molecular electronics and nanotechnology (envisioned molecular synthesis and fabrication) within the proposed enabling 3D^{3 (Hardware-Software-Nanotechnology)} technology.
- 2. A novel concept in the design of Integrated Circuits (ICs) and ^MICs in 3D space was developed and demonstrated. The proposed Super Large Scale Integration (SLSI) design was supported by the software developed. The design was performed for ICs by utilizing hypercubes (enhancing the design and data structure capabilities) within the envisioned molecular implementation by neuronal hypercells ([®]hypercells). Hypercubes (ICs design) and [®]hypercells (^MICs implementation by molecular processing/memory hardware primitives) were designed. The performance and capabilities were assessed at device and system levels. Aggregated [®]hypercells form 3D [®]hypercell lattices implementing processing platforms. At the system level, benchmarking ICs, which have been widely used to evaluate and assess Very Large Scale Integration (VLSI) and Ultra Large Scale Integration (ULSI) designs, were examined as proof-of-concept 3D ^MICs.
- 3. Biomolecular and molecular processing hardware solutions were studied. Organic molecules form complexes which can be utilized as enabling molecular electronic devices (^{ME}devices). Molecular gates (^Mgates) and ^Nhypercells are formed using ^{ME}devices. A 3D-topology *solid* ^{ME}device, engineered using monocyclic molecules, was modeled, simulated and analyzed. Components of the representative Computer Aided Design (CAD) software were developed to support the logic design tasks for 3D ^MICs. Combinational circuits, including 8- and 9-bit Arithmetic Logic Units (ALUs), were designed.

An enabling 3D³ technology was devised by utilizing a three-fold innovative solution:

- <u>Hardware</u> novel 3D-topology ^{ME} devices, enabling system organizations and architectures;
- <u>Software</u> technology-centric CAD tools supported by new design methods to accomplish the SLSI tasks for complex ^MICs;
- <u>Nanotechnology</u> molecular technology to synthesize ^Nhypercells, ^MICs, modules and platforms. This 3D³ technology ensures super-high-performance processing. We focused on development of a feasible, practical, affordable and superior technology for massive parallel distributed computing. The proposed technology allows one to perform design coherently integrating design and synthesis tasks at the device/gate and system levels.

We departed from the conventional, two-dimensional (2D) topology, organization and architecture of ICs and processing platforms, VLSI, ULSI and post ULSI design concepts and 2D Complimentary Metal Oxide Semiconductor, (CMOS) paradigms. A novel 3D³ technology, as implemented, will ensure:

- 1. Enormous military advantages because envisioned super-high-performance platforms will guarantee information processing preeminence, computing superiority and memory supremacy;
- 2. Very strong commercial potential with immediate applications in design of new generations of preeminent processors and memories;
- 3 Sound technology transfer feasibility to future Air Force systems.

1. INTRODUCTION

The overall objective of this project was to start the development of a novel 3D³ (Hardware-Software-Nanotechnology) technology for super-high-performance three-dimensional (3D) molecular/biomolecular computing and processing platforms to accomplish demanding mission-specific computing to support Air Force tasks. The specific objectives were:

- 1. Utilizing a unified bottom-up/top-down synthesis taxonomy, design super-high-performance computing (processing) platforms implemented using molecular integrated circuits (^MICs), devise innovative organizations/architectures and assess 3D³ technology researching novel hardware, software, design methods and molecular electronics (nanotechnology) solutions.
- Develop and demonstrate logic design methods in synthesis of 3D ^MICs for computing platforms. Perform the 3D-centered design of super-complex combinational circuits by using hypercubes as homogeneous aggregated data structure assemblies. Assess technology-centric Super Large Scale Integration (SLSI), and analyze the implementation of ^MICs utilizing neuronal hypercells (⁸hypercells) as the molecular hardware primitives. Develop and apply performance indexes to evaluate molecular electronics and ^MICs.
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- 3. Propose molecular electronic devices (^{ME}devices). For a multi-terminal ^{ME}device, perform modeling and analysis of electron transport to assess the applicability of ^{ME}devices for molecular gates (^Mgates), ^Nhypercells and ^MICs. Develop and demonstrate the fundamentals of the CAD-supported synthesis, design, analysis and evaluation methods. Start the development of proof-of-concept CAD tools, where representative CAD software should perform illustrative design and analysis tasks at the device and system levels. Demonstrate the design for combinational circuits, including an 8- or 9-bit arithmetic logic unit (ALU).

Research at the system and device level was focused on the solution of a number of major problems. The technology developments were concentrated on the following three major tasks:

- 1. Develop a unified bottom-up and top-down synthesis taxonomy in order to design super-highperformance computing (processing) platforms within novel 3D topologies and enabling organizations/architectures. Assess 3D³ technology which utilizes three major innovations, e.g., 3D ^MICs (molecular electronics), software, and molecular fabrication technology.
- Propose and start development of a computationally efficient technology-centric SLSI design for circuits in 3D. Design ^MICs using hypercubes (data structures) and implement the designed ^MICs using [™]hypercells. Derive baseline performance estimates for the molecular electronic system.
- 3. Study biomolecular and molecular processing hardware solutions. Analyzing organic molecules, research multi-terminal ^{ME}devices which comprise of ^Mgates and ^ℕhypercells. Model and obtain the baseline performance characteristics for a 3D-topology *solid* ^{ME}device. Start the developments of components of the representative CAD tools to support the logic design tasks for 3D ^MICs. Design combinational circuits, including an 8- or 9-bit ALU.

For the aforementioned major tasks, in order to complete the overall and specific objectives, *Microsystems and Nanotechnologies* successfully accomplished the following:

For the **Statement of Work, SOW Task 1**, *Microsystems and Nanotechnologies* developed and demonstrated a nanotechnology-centric synthesis taxonomy to design super-high-performance computing and processing platforms. A unified bottom-up and top-down synthesis taxonomy to concurrently support

3D³ technology was developed. This synthesis taxonomy was evaluated emphasizing different molecular (nanotechnology) hardware and processing paradigms.

For the **SOW Task 2**, *Microsystems and Nanotechnologies* developed and demonstrated a new computationally efficient method in the design of ^MICs. This technology-centric design results in the synthesis of complex ^MICs using hypercubes to represent data structures in 3D, and implementation of ^MICs by [®]hypercells. The proposed concept allows one to design and implement innovative organizations and architectures. The design was accomplished by developing proof-of-concept software supporting the 3D³ technology. Performance characteristics were derived or estimated in order to obtain coherent indexes and metrics at the device and system levels.

For the **SOW Task 3**, *Microsystems and Nanotechnologies* examined the feasibility, soundness and baseline performance characteristics of prospective molecular and biomolecular devices which form molecular and biomolecular processing hardware. With the emphasis on foreseen synthesis technologies, fabrication feasibility, soundness and affordability, models of monocyclic organic molecules were utilized as multi-terminal solid ^{ME}devices to engineer ^Mgates which form ^Nhypercells and ^{MICs.} The electron transport in a *solid* ^{ME}device was modeled to obtain the baseline device characteristics and performance estimates. The representative proof-of-concept CAD tools in the logic design of ^MICs were developed and demonstrated for ALUs and other combinational circuits.

2. METHODS, ASSUMPTIONS, AND PROCEDURES

Solution (Methods) – An innovative $3D^3$ technology was based on the design of computing (processing) platforms and ^MICs utilizing a three-fold solution:

- 1. Novel hardware utilizing enabling 3D topologies, organizations and architectures;
- 2. New software and technology-centric CAD tools supported by advanced design methods to perform SLSI design,
- 3. Nanotechnology-centered fabrication and implementation of molecular processing hardware.

This led to:

- 1. New organization and enabling architectures coherently supported by the SLSI design of ^MICs utilizing a technology-centric software and CAD tools;
- Novel device physics and enabling device/system capabilities utilizing novel phenomena, effects and abilities of 3D-topology ^{ME} devices and ^MICs;
- 3. Bottom-up fabrication.

The $3D^3$ technology model developed in this project provides evidence of soundness, feasibility and achievable super-high-performance reaching the fundamental limits of quantum mechanics (molecular device level) and systems capabilities (novel topologies/organizations/architectures). This project focused on development of a feasible, practical, affordable and superior technology for massive parallel distributed computing and processing. The $3D^3$ technology that was developed allows one to perform design coherently, integrating synthesis tasks at the device/gate and system levels.

By performing fundamental and applied studies *Microsystems and Nanotechnologies* devised an enabling $3D^3$ technology which promises to ensure processing preeminence, computing superiority and memory supremacy. By introducing the $3D^3$ technology, we departed from conventional planar ICs

topology, classical organization/architecture, CMOS technology, and VLSI/ULSI design. A paradigm of massively parallel distributed (pipelined due to systolic processing) processing in 3D was utilized using devised hypercubes, with the hardware implementation by [®]hypercells. In general, hypercubes significantly increase the number of bits of information processed and exchanged to compute complex switching functions, while [®]hypercells enable 3D topology, fused cyclic processing-and-memory organization and reconfigurable networking-and-processing neuromorphological architecture. The logic design and mappings were simplified by the use of linear decision diagrams and linear systolic arrays for data processing and manipulation. The assumptions made were: (1) Utilization of envisioned molecular electronics to implement ^Mgates forming *modular* [®]hypercells and ^MICs; (2) Availability of fabrication technology readiness.

3. RESULTS AND DISCUSSIONS

3.1. MOLECULAR COMPUTING AND PROCESSING PLATFORMS: INTRODUCTION AND PERFORMANCE ESTIMATES

3.1.1. Microelectronics and Molecular Electronics

To design ^MIC-comprised processor and memory platforms, one must apply novel paradigms and which are based on the use of novel 3D-topology devices, enabling technologies organizations/architectures, sound bottom-up fabrication, etc. Tremendous progress has been accomplished within the last 60 years in microelectronics, e.g., from inventions and demonstration of functional solid-state transistors to fabrication of processors that comprise billions of transistors on a single die. Current high-yield 65 nm CMOS technology node ensures minimal features ~65 nm, and fieldeffect transistors (FETs) were scaled down to achieve channel lengths below 30 nm. Using this technology, an ~500,000 nm² foot-print area was achieved by Intel for static random access memory (SRAM) cells. Optimistic predictions foresee that within 15 years the minimal feature of planar (twodimensional) solid-state CMOS-technology transistors may approach ~10 nm leading to the *effective* cell size for FETs $\sim 20\lambda = 400 \text{ nm}^2$. However, the projected scaling trends are based on a number of assumptions and foreseen enhancements. Though the cell dimension of the scaled down FETs can reach 400 nm², the overall prospects in microelectronics (technology enhancements, device physics, device/circuits performance, design complexity, cost and other features) are troubling. The near-absolute limits of CMOS-centered microelectronics may be reached in the next decade. The general trends, prospects and projections are reported in the International Technology Roadmap for Semiconductors [1]. The device size- and switching energy-centered version of the first Moore's law for high-yield roomtemperature mass-produced microelectronics is reported in Figure 1 for past, current (90 and 65 nm) and foreseen (45 and 32 nm) CMOS technology nodes. For the switching energy, one uses eV or J, and 1 $eV=1.602176462 \times 10^{-19}$ J. Intel expects to introduce the 45 nm CMOS technology node in 2007. The envisioned 32 nm technology node is expected to emerge in 2010. Expected progress in the base-line characteristics and scaling has already slowed down due to encountered fundamental and technological challenges and limits [1-9]. Correspondingly, new solutions and technologies have been sought and assessed. Performance and functionality at the device and system levels can be significantly improved by utilizing novel phenomena, employing innovative topologies / organizations / architectures, enhancing device functionality, increasing density, improving utilization, and increasing switching speed. Molecular electronics (nanoelectronics) is expected to ensure superior performance and capabilities. It is foreseen

that, in order to ensure the projected microelectronics scaling trends, the cost of facilities to fabricate *nanoscale* microelectronics may reach hundreds of billion dollars by 2020.



Figure 1. Envisioned molecular (nano) electronics advancements and Moore's laws for microelectronics

Existing superb bimolecular processing / memory platforms and progress in molecular electronics provide evidence of fundamental soundness and technological feasibility for molecular electronics. Some data and expected developments, reported in Figure 1, are subject to adjustments because it is difficult to accurately foresee the fundamental development and maturity of prospective technologies due to the impact of many factors. It may be expected, that by 2025-2030 the core modules of super-high-performance processing (computing) platforms may be implemented using ^MICs. The emergence of molecular electronics and processing platforms is pervasive and irreversible. However, these high-risk high-payoff areas will require immense research and technology development efforts which largely depend on readiness, commitment, acceptance, investment, infrastructure, innovations and market needs.

The dominating premises of molecular (nano) processing and computing have a solid biological association. In fact, there exist a great number of superb molecular systems and platforms that utilize biological molecules. They possess profoundly different processing and memory devices, modules and systems from current electronics systems. Device-level biophysics operations are based on electrochemomechanically-induced transitions, interactions and events, while the system-level fundamentals are expected to rely on integrated processing-and-memory organization and neuromorphological reconfigurable architectures [4]. Real-time 3D image processing is ordinarily accomplished by primitive insects and vertebrates that have less than 1 million neurons. To perform these and other immense processing tasks, less than 1 μ W is consumed. However, real-time 3D image processing cannot be performed by even envisioned processors with trillions of transistors, 1 THz device switching speed, 10 GHz circuit speed, 1×10^{-16} J device switching energy, 1×10^{-16} J/bit writing energy, and 10 nsec read time. This is evidence of superb biomolecular processing efficiency that cannot be surpassed by any envisioned standard microelectronics enhancements and innovations. Biomolecular processing provides a sound foundation to the overall soundness of envisioned molecular computing and processing platforms.

Molecular devices and ^MICs can operate due to electron or ion transport, photon interaction, biomolecular interactions, transitions, etc. Distinct classes of devices, basic physics, phenomena exhibited, effects utilized and fabrication technologies can be profoundly different. Molecular electronics, theory, engineering practice and technology will require revolutionary advances compared with microelectronics theory and CMOS technology. From a 3D-centered topology, organization, architecture standpoint, *solid* and *fluidic* molecular electronics evolution mimics (to some degree) biomolecular solutions. Compared with the most advanced CMOS processors, molecular platforms will greatly enhance functionality and processing capabilities, radically decrease dimensionality, latency, power and execution time, as well as drastically increase device density, utilization and memory capacity. Many difficult problems at the device and system levels must be addressed, researched and solved. Development is required in design, analysis, optimization, aggregation, routing, evaluation, reconfiguration, verification and evaluation.

3.1.2. Performance Estimates.

Combinational and memory ^MICs can be designed as aggregated hypercubes and implemented as ^Nhypercells [4, 6, 7]. At the device level, one examines functionality, studies characteristics and estimates performance of 3D-topology ^{ME}devices. The device- and system-level performance measures are of great interest. To analyze the device energetics, examine the switching energy, transit speed, and other baseline characteristics, we applied quantum mechanics [4-7].

Photon Absorption and Transition Energetics – A photon is an emitted or absorbed quantum of electromagnetic energy, and each photon of frequency $v (v=c/\lambda)$ has an energy E=hv, where h is the Planck constant, $h=6.62606876\times10^{-34}$ J-sec, c is the speed of light and λ is the wavelength. Thus, the energy of a single photon is given by $E=hc/\lambda$. The maximum absorbance for typical bio-molecule, rhodopsin is 498 nm. For this wavelength, one finds $E=4\times10^{-19}$ J. This energy is sufficient to ensure transitions and functionality. Thus, the energy of a single photon, which is $E=4\times10^{-19}$ J, ensures the functionality of a molecular complex of 348 amino acids composed of ~5000 atoms. We derived the excitation energy (signal energy) which is sufficient to ensure electrochemomechanically-induced state transitions and interactions leading to processing. This provides evidence that ~1×10⁻¹⁹ to 1×10⁻¹⁸ J of energy is required to accomplish the state transitions for molecular aggregates in the biomolecular processing hardware.

Energy Levels and Energetics of ^{*ME}</sup><i>Devices* – In ^{ME}devices, one can calculate the energy required to excite an electron and the allowed energy levels can be quantized. The application of quantum mechanics results in the expression for the quantized energy, and for a hydrogen atom:</sup>

$$E_n = -\frac{m_e e^4}{32\pi^2 \varepsilon_0^2 \hbar^2 n^2},$$

where m_e is the electron effective mass, e is the electron charge, ε_0 is the free space permittivity constant, \hbar is the modified Planck constant and n is the principal quantum number.

The energy levels depend on the quantum number *n*. As *n* increases, the total energy of the quantum state becomes less negative, and $E_n \rightarrow 0$ if $n \rightarrow \infty$. The state of lowest total energy is the most stable state for the electron. The normal state of the electron for a hydrogen (one-electron atom) is at n=1.

The conversion 1 eV=1.602176462×10⁻¹⁹ J is commonly used, and $E_{n=1}$ =-2.17×10⁻¹⁸ J=-13.6 eV. For n=2, n=3 and n=4, we have $E_{n=2}$ =-5.45×10⁻¹⁹ J, $E_{n=3}$ =-2.42×10⁻¹⁹ J and $E_{n=4}$ =-1.36×10⁻¹⁹ J. The energy difference between the quantum states n_1 and n_2 is

$$\Delta E = E_{n1} - E_{n2}, \text{ and } \Delta E = E_{n1} - E_{n2} = \frac{m_e e^4}{32\pi^2 \varepsilon_0^2 \hbar^2} \left(\frac{1}{n_2^2} - \frac{1}{n_1^2}\right),$$

where $\frac{m_e e^4}{32\pi^2 \varepsilon_o^2 \hbar^2} = 2.17 \times 10^{-18} \text{ J} = 13.6 \text{ eV}.$

The excitation energy of an exited state n is the energy above the ground state, e.g., for the hydrogen atom one has $(E_n - E_{n=1})$. The first exited state (n=2) has the excitation energy $E_{n=2} - E_{n=1} = -$ 3.4+13.6=10.2 eV. Using n, one may estimate ΔE deriving the energy required to ensure the quantum transitions and interactions.

For many-electron atoms, an atom in its normal (electrically neutral) state has Z electrons and Z protons. Here, Z is the atomic number. For boron, carbon and nitrogen, Z=5, 6 and 7, respectively. By evaluating the average value for the radius of the shell, the effective nuclear charge Z_{eff} is found. The common approximation to calculate the total energy of an electron in the outermost populated shell is

$$E_n = -\frac{m_e Z_{eff}^2 e^4}{32\pi^2 \varepsilon_0^2 \hbar^2 n^2}$$
, and $E_n = -2.17 \times 10^{-18} \frac{Z_{eff}^2}{n^2}$ J

The effective nuclear charge Z_{eff} is found by using the electron configuration. For boron, carbon, nitrogen, silicon and phosphorus, three commonly used Zeff are (Slater, Clementi and Froese-Fischer techniques):

2.6, 2.42 and 2.27 (for B), 3.25, 3.14 and 2.87 (for C), 3.9, 3.83 and 3.46 (for N),

4.13, 4.29 and 4.48 (for Si) and 4.8, 4.89 and 5.28 (for P).

Taking note of the electron configurations for the above mentioned atoms $(Z/n\approx 1)$, one concludes that ΔE is from $\sim 1 \times 10^{-19}$ to 1×10^{-18} J. If one supplies the energy greater than E_n to the electron, the energy excess will appear as kinetic energy of the free electron. The transition energy should be adequate to excite electrons. For different atoms and molecules with different exited states, as prospective solid ^{ME}devices, the transition (switching) energy is estimated to be $\sim 1 \times 10^{-19}$ to 1×10^{-18} J. This energy estimate is in agreement with biomolecular devices.

Device Switching Speed. The transition (switching) speed of ^{ME} devices largely depends on the device physics and phenomena utilized. Considering the electron transport, one may assess the lower bounds for a switching frequency using the number of electrons to ensure on/off switching. For example, for 1 nA current, the number of electrons that cross the molecule per second is $1 \times 10^{-9} / 1.6022 \times 10^{-10}$ 19 =6.24×10⁹, and is related to switching capabilities. The maximum carrier velocity places an upper limit on the frequency response of semiconductor devices and ^{ME}devices. Theoretically, the switching can be accomplished by a single electron. Using the Bohr postulates, the average velocity of an optically-exited electron is $v = \frac{Ze^2}{4\pi\varepsilon_0\hbar n}$. Taking note that for all atoms $Z/n\approx 1$, one finds the orbital velocity of an optically-

exited electron to be $v=2.2\times10^6$ m/sec or $v/c\approx0.01$. Taking note of $E=mv^2/2$, we obtain the electron velocity as a function of energy, e.g., $v(E) = \sqrt{\frac{2E}{m}}$. Letting $E=0.1 \text{ eV}=0.16 \times 10^{-19} \text{ J}$, one finds $v=1.88 \times 10^5$

m/sec. Assuming 1 nm length of the electron path, the traversal time is $\tau = L/v = 5.33 \times 10^{-15}$ sec. Hence, ^{ME} devices can operate at high switching frequency. However, one may not conclude that the device switching frequency to be utilized is $f=1/\tau$ due to device physics specifics (number of electrons, heating, interference, potential, energy, etc.), system-level functionality, circuit specifications, etc. Reported estimates indicate that the electron velocity in ^{ME}devices exceeds the carrier saturated drift velocity in semiconductors.

System Level Processing Performance Estimates. In reporting the performance estimates, we focus on molecular electronics, basic physics and our envisioned solutions. The topology of envisioned molecular devices and systems are analogous to the 3D-centered topology of biomolecular processing platforms. Aggregated brain neurons perform superb information processing, perception, learning, robust reconfigurable networking, memory storage and other functions. The number of neurons in the human brain is estimated to be ~ 100 billion, while mice and rats have ~ 100 million neurons. Flies accomplish real-time precisely coordinated motion control with a remarkable actuation and visual system which maps the relative motion using retinal photo-detector arrays. The information from the visual system and sensors is transmitted and processed at the nanoseconds range requiring uW of power. The dimension of the neuron is $\sim 10 \,\mu\text{m}$, and the density of neurons is thousands of neurons in mm³. The biophysics and mechanisms of biomolecular information processing are not fully comprehended. Performing enormous information processing tasks with immense performance (speed, accuracy and robustness) that are far beyond foreseen capabilities of envisioned parallel vector processors (that perform signal and data processing), the human brain consumes only ~20 W. Only some of this power is required to accomplish information and signal/data processing. This contradicts some postulates of slow processing, immense delays, high energy/power requirements, low "switching speed" and other hypotheses. The human retina has 125 million rod cells and 6 million cone cells, and this enormous data stream, among with other tasks, is processed in real-time. As demonstrated above, ^{ME}devices can operate with the estimated required transition energy $\sim 1 \times 10^{-18}$ J, discrete energy levels (ensuring multiple-valued logics and memory) and femtosecond transition dynamics promising exceptional device performance [4]. These 3D-topology ^{ME} devices result in the ability to design super-high-performance processing and memory platforms (systems) with novel architectures ensuring unprecedented capabilities including massive parallelism. robustness, reconfigurability, etc.

Distinct performance measures, estimates and indexes are used. Figure 2 reports some baseline performance estimates for profoundly different paradigms (microelectronics versus molecular electronics that are distinguished by distinct topologies, organizations and architectures), e.g., transition (switching) energy, delay time, dimension and number of modules/gates. It was emphasized that device physics and system organization/architecture are dominating premises as compared to the dimensionality or number of devices. Due to limited demonstrated experimental results as well as the attempts to use four performance variables, some performance measures and projected estimates reported in Figure 2 are expected to be refined and adjusted in the future.

Molecular electronics and ^MICs can utilize diverse molecular primitives and devices that: (1) Operate due to different physics, for example, electron transport, electrostatic transitions, photon emission, conformational changes, etc.; (2) Exhibit distinct phenomena and effects. Therefore, biomolecular, *fluidic*, *solid* and *hybrid* molecular devices and systems will exhibit distinct performance. As demonstrated in Figure 2, advancements are envisioned towards 3D *solid* molecular electronics departing from biomolecular processing by utilizing a familiar solid-state microelectronics solution. In Figure 2, 3D-topology neuron operation is represented as a biomolecular information processing and memory module (system).



Device Transition (Switching) Energy [J]

- Figure 2. Towards molecular electronics and computing (processing) platforms:
 - Revolutionary advancements: From 2D microelectronics to 3D molecular electronics
 - Evolutionary developments: From biomolecular to *solid* ^{ME}devices

3. 2. SYNTHESIS TAXONOMY

We developed a novel unified top-down/bottom-up synthesis taxonomy in design of computing and processing platforms. By utilizing this taxonomy, our goal was to perform:

- I <u>Top-down Synthesis</u>: We devised novel super-high-performance 3D computing platforms within a 3D fused processing-and-memory organization and a reconfigurable 3D networkingand-processing neuromorphological architecture. Molecular ICs were designed using advanced data structure methods by applying 3D hypercubes, and ^MICs (molecular processing hardware) were implemented as aggregated ^ℕhypercells composed from ^Mgates that are engineered from multi-terminal ^{ME}devices (atomic aggregates), see Figures 3.a and 3.b;
- II <u>Bottom-up Synthesis</u>: We synthesized ^{ME}devices from atomic complexes, arranged in functional molecular aggregates that comprise of ^Mgates within ^ℕhypercells and ^ℕhypercells lattices. We implemented the envisioned architectures and organizations by utilizing networked ^ℕhypercells which form ^MICs to realize the circuit design.



- Figure 3. (a) Three-dimensional molecular electronics: Hypercubes D_{ijk} implemented by ^Nhypercells (atomic or molecular aggregates) composed from ^Mgates that integrate multi-terminal ^{ME}devices engineered from atomic complexes;
 - (b) Concurrent synthesis and design at system, subsystem and gate (device) levels.

Major Innovations: The modeled $3D^3$ technology and computing platform utilize <u>five major</u> innovations at the system and device levels to support top-down/bottom-up synthesis:

- 1. Enabling architectures, organization, topologies, aggregation and networking;
- 2. Unique phenomena, effects and capabilities (quantum tunneling, parallelism, robustness, etc.);
- 3. Novel multi-terminal ^{ME}devices which form ^Mgates, [®]hypercells and ^MICs;
- 4. Nanotechnology: Molecular and organic synthesis as a *bottom-up* fabrication technology;
- 5. SLSI as a CAD-supported synthesis, design, analysis and evaluation paradigm.

Bottom-Up/Top-Down Synthesis Taxonomy – High-performance computing and processing platforms can be synthesized using hypercubes D_{ijk} which can be implemented utilizing ^Nhypercells. This provides an analogy to the superb 3D biomolecular processing platforms. A coherent synthesis must be performed to accomplish all tasks within the specific flow-map. From the design prospective, 3D molecular synthesis and aggregation are not analogous to the CMOS layout synthesis. Furthermore, VLSI/ULSI design is based on conventional CMOS fabrication technology, 2D (planar) organization, conventional architectures and solid-state gates with FETs and bipolar junction transistors (BJTs). The proposed 3D³ technology utilizes a unified top-down (system level) and bottom-up (device/gate level) synthesis taxonomy within an *x*-design flow map which is depicted in Figure 4. Thus, the core 3D design themes are integrated within four domains:

- Devising (synthesis) with validation
- Design–optimization

• Modeling–analysis–evaluation

• Nanotechnology–fabrication



Figure 4. Top-down and bottom-up synthesis taxonomy with *x*-design flow-map.

Data Structure, Decision Diagram, and Hypercubes - For 2D CMOS ICs, the decision diagram (unique canonical structure) is derived as a reduced decision tree by using topological operators. In contrast, for 3D ^MICs, a new class of decision diagrams and synthesis methods must be developed [4, 10, 11]. We used a novel linear decision diagram which is mapped by 3D hypercubes. This 3D hypercube (cube, pyramid, hexagonal or other 3D topological clusters) uses a unique canonical structure which is a reduced decision tree. Hypercubes were found by using topological operators, e.g., deleting and splitting nodes. Optimal linear decision diagrams were mapped to the 3D hypercubes. By mapping the 3D molecular technology, the hypercube structures ensure synthesis specificity. We modeled optimal topology mapping and suboptimal technology-specific topology mapping of complex switching functions. The major optimization criteria were: (1) minimization of decision diagram nodes and circuit terminals; (2) topological structures (linear arithmetic versus nonlinear arithmetic that leads to simple synthesis and straightforward embedding of linear decision diagrams into 3D topologies); (3) minimization of path length in decision diagrams; (4) simplified routing; (5) minimization of circuit complexity. These criteria resulted in power dissipation reduction, verification simplicity, testability enhancement, as well as other important features. For example, switching power is not only a function of device/gate-realization (BJTs and FETs for CMOS), but also a function of circuit topology, design methods, routing, dynamics, switching activities and other factors that can be optimized thereby reducing the switching power and losses.

Neuronal Hypercells – As was emphasized, [%]hypercells are formed by ^Mgates which are engineered from ^{ME}devices. Performance and characteristics of molecular complexes are drastically affected by the atomic (molecular) structures, aggregation, bonds, atomic orbitals, electron affinity, ionization potential, arrangement, sequence, assembly, folding and other features. We focused our efforts on design of ^{ME}devices, ^Mgates and [%]hypercells which ensured desired switching (logic) functions, practical electronic characteristics, desired performance, specified geometry (conformation), and functionality. Super-high bandwidth (switching frequency), superior density, low power, low voltage, desired *I–V* characteristics, enhanced functionality, noise immunity, robustness and other characteristics were ensured through a coherent design. Device performance and characteristics can be changed and optimized by altering and controlling quantum processes, transitions, interactions, etc. For ^{ME}devices, the number of quantum wells, barrier width, energy profile, tunneling length, propagation path, dielectric constant and other features can be adjusted and optimized by designing molecules with controlled atomic sequences, bonds, branches, etc. The goal is to ensure optimal achievable performance and assess it using the performance evaluation metrics. The interactive synthesis taxonomy is integrated with the systemlevel tasks to be performed as reported in Figure 4.

Reconfigurable Networking-and-Processing Neuromorphological Architectures – The neuroarchitectronics paradigm served as the basis for the design of novel super-high-performance molecular computing and processing platforms which are envisioned to be implemented utilizing 3D-topology ^MICs. The networked neuronal aggregates were prototyped by [%]hypercell lattices, which ensure a fused processing-and-memory organization, while reconfigurable networking-and-processing neuromorphological architecture was ensured due to inherent 3D-topology, enabling performance, enhanced capabilities (routing, networking, etc.) and other advantages of the 3D³ technology. For example, the modular [%]hypercell can implement the switching function of arbitrary complexity (performing multiple-valued combinational logics and processing) as well as store data. Figure 5 illustrates the organization and architecture of the computing and memory platforms.



Figure 5. Processing and memory platforms: Fused processing-and-memory organization and reconfigurable networking-and-processing neuromorphological architecture

Reconfigurable computing is an established term that applies to any device or primitive which can be configured, at run-time, to implement a function utilizing a specific hardware solution. A reconfigurable device should possess adequate logic, reprogramming and routing capabilities to ensure reconfiguration features, as well as to compute a large set of functions. The reconfigured ^{ME}device performs a different set of functions. Consider a ^Mgate with binary inputs A and B. Using the outputs to be generated by the universal logic gate, one has the following 16 functions: 0, 1, A, B, \overline{A} , \overline{B} , A+B, $\overline{A} + \overline{B}$. $\overline{A} + \overline{B}$, \overline{AB} , \overline{AB} , \overline{AB} , \overline{AB} , \overline{AB} and $\overline{AB} + \overline{AB}$. The standard logic primitives (AND, NAND, NOT, OR, NOR and other) can be implemented using a Fredkin gate which performs conditional permutations. Consider a ^Mgate with a *switched* input A and a *control* input B. As illustrated in Figure 6, the input A is routed to one of two outputs, conditional on the state of B. The routing events change the output switching function which is AB or \overline{AB} .



Figure 6. Molecular gate schematic

Utilizing the proposed molecular processing paradigm, *routable* molecular universal logic gates can be designed and implemented using neuromorphological architectures. We defined a *routable* molecular universal logic gate as a reconfigurable combinational gate that can be reconfigured to realize specified functions of its input variables. These *routable* molecular universal logic gates can realize logic functions using multi-input variables. These *routable* molecular universal logic gates can realize logic functions using multi-input variables. These *routable* molecular universal logic gates can realize logic functions using multi-input variables. Figure 7 schematically depicts the proposed routing concepts for reconfigurable logic [4]. The typified 3D-topologically reconfigurable routing is accomplished through the connecting/disconnecting of ^Mgates which perform processing and memory storage. For illustrative purposes, Figure 7 demonstrates reconfiguration of 5 ^Mgates within 10 ^Nhypercells depicting a reconfigurable networking-and-processing in 3D. The inputs are denoted as x_1 , x_2 , x_3 , x_4 , x_5 and x_6 . The use of reconfigurable routing uniquely enhances and complements the capabilities of the ^Nhypercell solution. In general, one may not be able to route just any output of any gate/hypercell/module to just any input of any other gate/hypercell/module. There are synthesis constraints, selectivity limits, complexity to control the spatial motion of electrons as the *routers*, as well as other limits which should be integrated in the design.



Figure 7. Reconfigurable routing and networking

Utilizing molecular electronics, one can control charged carriers (electrons) and steer electrons in 3D accomplishing directed routing and adaptive spatial networking. We modeled the *processing* and *routing* transition functions F_p and F_r which describe previous *processing* and *routing* states to the resulting new states in $[t, t_+], t_+>t$. The output evolution is given as $\mathbf{y}(t_+)=F_i[t,\mathbf{x}(t),\mathbf{y}(t),\mathbf{u}(t)]$, where \mathbf{x} and \mathbf{u} are the state and control vectors. For example, \mathbf{u} leads to the *routing* control with the resulting routing and reconfigurable networking. The reconfiguration is described as $P \subset X \times Y \times U$, where X, Y and U are the input, output and control sets.

Design Rules – ^MICs can be synthesized through hierarchical synthesis motifs utilizing ^Nhypercells as molecular hardware primitives [4]. One may envision 3D directly interconnected molecular electronics utilizing a direct device-to-device aggregation. The ^{ME}device-^{ME}device interconnect can be accomplished as the chemical-bonding fabric (atomic bonding), and be energy-based (for example, utilizing the exchange/conversion/transmission of radiated and absorbed electromagnetic energy), etc. We designed reconfigurable ^MICs and developed complimentary software tools to cope with non perfect (partially defective and faulty) ^Nhypercells and circuits in arithmetic, control, input-output, memory and other functions. Molecular electronics will result in ^MICs with a significant number of entirely or partially defective and faulty devices and interconnects [4]. Reconfiguration along with redundancy ensures overall soundness. The circuit reconfigurability capability is determined by the yield, complexity, software abilities (to detect, identify and tolerate the hardware deficiencies), etc. Adaptability and

reconfigurability can be achieved through hardware diagnostics, testing and analysis with the following mapping, matching, switching, controlling, rerouting and networking tasks performed by software [4]. In general, one designs, optimizes, builds, tests/evaluates and reconfigures ^MICs. We developed the following *design rules*:

- 1. Design and optimize ^MICs performing SLSI design;
- 2. Apply the *target* ^MICs realization using the *modular* [&]hypercells;
- 3. Design a *specific* ^{\overline}hypercell *template* assessing the expected yield and error rates;
- 4. Analyze and perform the *bottom-up* synthesis developing and specifying the technology, processes and other tasks to synthesize ^MICs as an assembly of ^ℵhypercell aggregates;
- 5. Utilizing hierarchical
 - (i) random circuit assembly with random sequences, (ii) near-random assembly with near-random sequences, or (iii) ordered assembly with deterministic sequences,
 - specificity (terminal/interconnect-recognition, terminal/interconnect site recognition, selfbinding, paring and complimentary compliance of ⁸hypercells within node *lattices*),
 - nearest-neighboring ^{\%}hypercell placement motifs,
 - synthesize ^Nhypercell aggregates forming node *lattices* which should realize ^MICs;
- 6. Perform hardware/software-centered diagnostics, verification and testing;
- 7. Reconfigure, characterize, evaluate and validate ^MICs.

These *design rules* define the random, near-random or ordered (directed) ordering of ^{\aleph} hypercells and their aggregates. Using this hierarchical strategy, one ensures the soundness of the integrated design-synthesis-networking-and-reconfiguration tasks. This sub-optimal solution promises to ensure:

- 1. Affordability and high yield with potentially tolerable error rate;
- 2. Selectivity and specificity of ^{*}hypercells as processing and memory primitives;
- 3. Controllable self-assembling and robust binding/paring by utilizing ^{\&}hypercell-^{\&}hypercell and ^{\&}hypercell-interconnect uniformity, complimentary compliance and recognition;
- 4. Overall functionality.

3. 3. LOGIC DESIGN OF MOLECULAR ICS

3.3.1. Design of 3D Molecular Integrated Circuits: Data Structure, Decision Diagram and Hypercubes

The dimension of a decision diagram (number of nodes) is a function of the number of variables and the variables ordering. In general, the design complexity is $O(n^3)$. This complexity significantly limits the design capabilities in terms of IC complexity (number of gates) for which the design can be performed. The commonly utilized word-level decision diagrams further increase complexity due to processing of data in word-level format. Therefore, novel concepts are needed. We devised a sound software-supported design approach which features SLSI capabilities. In particular, novel methods in data structure representation and data structure manipulation were developed and demonstrated by the *Microsystems and Nanotechnologies* team to ensure design specifications and objectives. We applied linear word-level decision diagrams (LWDDs) accomplishing compact representation of logic circuits using linear arithmetical polynomials [10, 11]. The design complexity becomes O(n). The concept ensures compact representation of circuits compared with other formats and methods. The design algorithm is:

Function (Circuit) ↔ BDD Model ↔ LWDD Model ↔ Hypercube Realization

 \leftrightarrow ^MICs Implementation (^{\&}Hypercell Lattice) where BDD is a Binary Decision Diagram.

The hypercube we utilized is a homogeneous aggregated assembly for massive super-highperformance parallel computing. Switching theory was applied to design the 3D hypercubes. To perform logic design, graph-based data structures in 3D space were utilized [11]. The hypercube is a topological representation of a switching function by *n*-dimensional graph. The switching function *f* is given as: Coefficient

Switching Function
$$\Rightarrow \mathbf{L}_{\substack{i=0\\ \uparrow\\ \text{Operation}}}^{2^n-1} \mathbf{\Omega}_i^{(x_1^{i_1}\dots x_n^{i_n})} \Rightarrow \text{Form of Switching Function}$$

The data structure is described in matrix form using the truth vector F of a given switching function f as well as the vector of coefficients $\mathbf{\Omega}$. The logic operations are represented by **L**. The logic design in spatial dimensions is based on advanced methods and data structures in 3D. For hypercubes, the appropriate data structure of logic function and methods of embedding this structure in hypercubes must be found. We developed a three-step-solution in logic function manipulation to change the carrier of information from the algebraic form (logic equation) to the hypercube structure. In particular:

- Step 1: Logic function is transformed to the appropriate algebraic form (Reed-Muller, arithmetic or word-level in matrix or algebraic representation);
- Step 2: Derived algebraic form is converted to the graphical form (decision tree, decision diagram or logic network);
- Step 3: Obtained graphical form is embedded into hypercube.

Hence, the design is expressed as: Logic Function \Leftrightarrow Graph \Leftrightarrow N - Hypercube Structure . Step 1 step 2 Step 3

The linear word-level decision diagram (LWDD) allows one to perform the compact representation of logical circuits utilizing linear arithmetic polynomials (LPs). This approach ensures compact representation of circuits compared with other formats. The algorithm is given as

Function (Circuit) ↔ BDD Model ↔ LWDD Model ↔ Hypercube Realization

 \leftrightarrow ^MICs Implementation ([%]Hypercell Lattice).

The LWDD is imbedded in hypercubes resulting in circuits in a 3D space. The polynomial representation of logical functions ensures the description of a many-output function in a word-level format. The expression of a Boolean function f of n variables $(x_1, x_2, \dots, x_{n-1}, x_n)$ is

$$LP = a_0 + a_1 x_1 + a_2 x_2 + \dots + a_{n-1} x_{n-1} + a_n x_n = a_0 + \sum_{j=1}^n a_j x_j$$

The resulting mapping establishes LWDD $(a_0, a_1, a_2, \dots, a_{n-1}, a_n) \leftrightarrow LP$.

The nodes of LP correspond to a positive Davio expansion. Thus, LWDDs are obtained by mapping LPs where the nodes correspond to the positive Davio expansion, and functionalizing vertices related to the coefficients of the LPs. The LWDD design flow is: Primitive↔LP Model↔LWDD $Model \leftrightarrow Realization.$

The proposed LWDDs uniquely complement our $3D^3$ technology ensuring large-scale data manipulation and SLSI design capabilities. Our LWDDs can be used to perform logic design and circuitry mapping utilizing hardware description languages. For different ICs, we performed a proof-of-concept logic design using the concept reported. The goal was to perform the design and evaluate it by examining the number of nodes (N), number of levels, CPU time required to design decision diagrams, etc. Topological characteristics were evaluated using the volumistic quantity, total number of terminals,

number of intermediate nodes and other parameters as reported in section 3.5.2, see Tables 1 and 2. Time and memory complexity is linearly upper-bounded by O(n) with respect to number of gates, while the conventional methods result in complexity $O(n^3)$. The concept results in:

- 1 Coherent algebraic representation of manipulation of complex switching functions;
- 2 Tractable matrix representation and manipulations;
- 3 Graph-based representation, as found using decision trees, decision diagrams and logic networks;
- 4 Data structures embedded into hypercubes.

The inner and outer hypercubes are depicted in Figure 8. Each 3D hypercube carries limited information because the number of nodes and links is limited. Hypercubes can be aggregated in complex aggregates representing data structures of arbitrary complexity as illustrated in Figure 8. The reported design allows one to carry out the SLSI design to implement enabling organizations and architectures.



Figure 8. Three-dimensional hypercubes and hypercube aggregate forming ^MICs

Massive parallelization is due to the fact that data structures are embedded into hypercubes. Furthermore, logic functions can be represented by word-level decision trees and diagrams. Thus, there are two unique parallelization sources that result in massive parallel computing:

- 1 *Natural* parallelism of 3D hypercubes and ^MICs (decision trees which represent logic functions are embedded into hypercubes);
- 2 *Enhanced* parallelism due to the word-level representation of logic functions (each node performs logic computations in parallel).

Hypercubes for FPGA – Hierarchical FPGAs are mapped by multi-input – multi-output switching. Conventional FPGA clusters are organized as 2D macro clusters, while 3D FPGAs can be implemented by hypercubes. Furthermore, hypercubes consist of clusters that can be patterned to produce multidimensional arrays.

3.3.2. Hypercube Design

The binary tree is a networked architecture that carries information about dual connections of each node. The binary tree also carries information about functionality of the logic circuit and topology. The nodes of the binary tree are associated with the Shannon and Davio expansions with respect to each variable and coordinate in 3D. A node in the binary decision tree realizes the Shannon decomposition $f = x_i f_0 \oplus x_i f_1$, where $f_0 = f|_{x_i=0}$ and $f_1 = f|_{x_i=1}$ for all variables in *f*. Thus, each node realizes the Shannon expansion, and the nodes are distributed over levels. The classical cube contains 2^n

nodes, while the hypercube has $2^n + \sum_{i=0}^n 2^{n-1}C_i^m$ nodes in order to ensure a technology-specific design of

^MICs. The hypercube consists of terminal nodes, intermediate nodes and roots. The most straightforward implementation is provided by using molecular multiplexers (^MMUX). However, other ^Mgates can be utilized as well. The design steps are:

- Step 1: Connect the terminal node with the intermediate nodes;
- Step 2: Connect the root with two intermediate nodes located symmetrically on the opposite faces;
- Step 3: Pattern the terminal and intermediate nodes on the opposite faces and connect them via the root.

There are several methods for representing logic functions. A hypercube, proposed as a core solution, is a homogeneous aggregated assembly for massive super-high-performance parallel computing. We applied enhanced switching theory integrated with a novel logic design concept [11]. In the design, the graph-based data structures and 3D circuit topology were utilized. The hypercube is a topological representation of a switching function by an *n*-dimensional graph. In particular, the switching function *f* is given as

Switching Function

$$f \Rightarrow \mathbf{L}_{\substack{i=0\\ \uparrow\\ \text{Operation}}}^{2^{n}-1} \mathbf{K}_{i} (x_{1}^{i_{1}}...x_{n}^{i_{n}}) \Rightarrow form of Switching Function}_{f_{F}}.$$

The data structure is described in matrix form using the truth vector F of a given switching function f as well as the vector of coefficients K. The logic operations are represented by L. Hypercubes compute f, and complex switching functions are implemented by ^{∞}hypercells. Figure 9 shows a hypercube to realize $f = \overline{x_1} x_2 \vee x_1 \overline{x_2} \vee x_1 x_2 x_3$. By utilizing the root and intermediate nodes at the edges, as shown in Figure 9, hypercubes can implement switching functions f of arbitrary complexity. This 3D solution coherently maps the device- and gate-level consideration by aggregating and networking ME gates by ^{*}hypercells. The logic design in spatial dimensions was based on advanced methods and enhanced data structures to satisfy a 3D topology for molecular hardware. The appropriate data structure of logic functions and methods of embedding this structure into hypercubes were found. The three-step-solution in a logic functions' manipulation, in order to change the carrier of information from the algebraic form (logic equation) to the hypercell structure, is:

- Step 1: Logic function is transformed to the appropriate algebraic form (Reed-Muller, arithmetic or word-level in matrix or algebraic representation);
- Step 2: Derived algebraic form is converted to the graphical form (decision tree, decision diagram or logic network);
- Step 3: Obtained graphical form is embedded in hypercubes, technologically implement able by [™]hypercells.

The design is expressed as

Step 1

Logic Function \Leftrightarrow Graph \Leftrightarrow Hypercube Structure \Leftrightarrow ^{\otimes} Hypercell Implementation . Step 2 Step 3-1 Sten 3-2



Figure 9. Hypercube which implements function f

The proposed concept results in:

- 1. Algebraic representation and robust rules of manipulation for complex switching logic functions;
- 2. Matrix representation and sound manipulation;
- 3. Consistency of logic relationships for variables and functions from the spectral theory viewpoint due to the use of matrix algebra;
- 4. Graph-based representation is found using decision trees, decision diagrams and logical networks;
- 5. Data structures are embedded into hypercubes.

3.3.3. Electronic Molecular Devices, Gates and [&]Hypercells: ^MIC Prospective

In VLSI design, resistor-transistor logic, diode-transistor logic, transistor-transistor logic, emittercoupled logic and other logic families have been used. All logic families and subfamilies have advantages and drawbacks, (within transistor-transistor logic, there are Schottky, low-power Schottky, advanced Schottky and others). In molecular electronics, one cannot adapt or utilize VLSI/CMOS-based design due to distinct fabrication technologies, topologies/organization/architectures, design rules, etc. This subsection focuses on some notional molecular device and system level features.

Molecular electronic devices offer significant advantages compared with microelectronic devices. For example, quantum effects result in multiple-valued *I–V* characteristics with very low current even at the maximum potential. This reduces power losses, enhances robustness, provides noise immunity, etc. Correspondingly, some logic families that are marginal in microelectronics may provide superior performance in molecular electronics. The molecular NOR (^MNOR) gate, realized using molecular resistor-device logic, is illustrated in Figure 10.a. In electronics, NAND is one of the most important gates. The molecular NAND (^MNAND) gate, designed by applying molecular diode-device logic, is shown in Figure 10.b. Molecular electronic devices operate utilizing phenomena and effects different compared with microelectronic devices, therefore in Figures 10.a and 10.b, we use different symbols to

designate molecular resistors $\neg \square \neg ({}^{ME}r)$, diodes $\checkmark ({}^{ME}d)$, and multi-terminal devices $\checkmark ({}^{ME}D)$.



Figure 10. Circuit schematics of two-input ^MNOR and ^MNAND gates

The design is accomplished in 3D space using hypercubes, and the designed circuits are implemented by ^{\aleph}hypercells. An example of a 3D ^{\aleph}hypercell to implement a logic function *f* is shown in Figure 11.a. Molecular multi-terminal devices $\stackrel{\frown}{\longrightarrow}$, with six or less inputs and outputs, are the corner nodes. Two-terminal devices (^{ME}diodes $\stackrel{\frown}{\longrightarrow}$ and ^{ME}resistors $\stackrel{\frown}{\longrightarrow}$) are shown. The input signals x_1, x_2 and x_3 , as well as the output switching function *f*, are documented. Three-dimensional aggregation and topology can be viewed to be biomimetics-centered. Molecular electronic devices and ^{\aleph}hypercells can be synthesized using engineered polypeptides, e.g., $[-N-C-C-]_n$ chains with side groups S_i . The implementation of a single ^{\aleph}hypercell utilizing engineered polypeptides is reported in Figure 11.b. Here, $(-N-C-C-)_n$ chains provide the structural skeleton (mechanical structure), while side groups S_i provide electron transport. Hence, S_i integrate ^{ME}devices engineered from organic molecules as reported in subsection 3.4.2. Figures 11.b and 11.c show how the 3D-topology interconnect is accomplished by S_i . ^{\aleph}Hypercells can be clustered and aggregated to form macrocell ^{\aleph}hypercell aggregates, thereby forming ^MICs.





(b) Implementation of the ^{\aleph}hypercell utilizing polypeptides with interconnected side R groups; (c) Implementation of the ^{\aleph}hypercell by M_{iik} with eight side groups S_{iik} . The ^MNAND gate, which is one of the most important gates, can be implemented utilizing molecular diode-device logic. The resulting ^Nhypercell schematic is documented in Figure 12. Molecular gates can be designed from an electronics and quantum mechanics viewpoint, and then synthesized using molecular nanotechnology which is based on organic synthesis. The design and analysis should be performed in order to optimize device characteristics, functionality, aggregate ability, gate topology, circuitry organization, and other features.



Figure 12. ^MGate (^MNAND) mapped by a single ^Nhypercell and its implementation.

3. 4. MULTI-TERMINAL MOLECULAR ELECTRONIC DEVICE

3.4.1. Biomolecules as Molecular Electronic Devices

Sequence-dependent self-assembled DNA and templated protein synthesis can be used to build patterned two- and three-dimensional structures with the desired geometrical topologies [12, 13]. Biomolecules accomplish information processing and memory storage through interactions that are not fully understood, however it is highly unlikely that processing is performed due to effects directly associated with electron flow. Therefore, biomolecular processing hardware does not possess ^{ME} devices or any their equivalents [4].

Some inorganic, organic and hybrid molecules, which exhibit desired electronic properties, are envisioned to be utilized in a new generation of ^{ME}devices in ^MICs [2-7, 14-20]. Processing, computing and memory platforms are envisioned to be designed and fabricated using self-assembled molecules utilized as multi-terminal ^{ME}devices. The *design rules* were reported in section 3.2. It is important to design and analyze functional high-performance ^{ME}devices which possess the desired electronic characteristics forming ^Nhypercells.

Biomolecules have been examined as ^{ME}devices in [21-24]. Contradicting conclusions and obscure results have been reported. Insulating, conducting and semiconducting properties were reported in the contact-biomolecule-contact and inter-biomolecular complexes [21-24]. Biomolecule synthesis, sequence, length, environment, alignment and other factors influence the electronic characteristics. In DNA, various experiments to examine the electron transport, *I*–*V* characteristics, conductance and other electronic properties were performed in [21-24] with limited success and contradicting results. Figure 13.a illustrates DNA attached to two electrodes. The electrode electrochemical potentials are denoted as V_{Fs} and V_{Fd} , while E_s and E_d are the self-energy functions of the "source" and "drain" as one uses the FET

terminology. Electrochemical potentials V_{Fs} and V_{Fd} vary. There is no electron transport if the system is in equilibrium, e.g., at $V_{Fs}=V_{Fd}$. The highest occupied molecular orbitals (HOMO) and lowest unoccupied molecular orbitals, (LUMO), as well as the Fermi level, are illustrated. Depending on the HOMO and LUMO levels, as well as E_F , the electron transport takes place through particular orbitals. Using broadening energies E_{Bs} and E_{Bd} , the electron flow rates are E_{Bs}/h and E_{Bd}/h . Guanine quartets (tubular sequences of G tetramers) were reported [22, 23]. Tetramers (G4) are the building blocks of a quadruplehelix forming G4-DNA. The hydrogen-bonded guanines arrange in a 2.3 nm diameter configuration. The prospective G4-DNA-based multi-terminal electronic device can be visualized as shown in Figure 13.b. Though G4-DNA aggregates were synthesized, the electronic characteristics have not been examined due to unsolved interconnect, manipulation and characterization engineering. Two- and multi-terminal DNAcentered devices, reported in Figures 13.a and 13.b, have a limited overall feasibility and soundness from both technological and fundamental standpoints.



Figure 13. a) Double-stranded DNA with two electrodes; b) G4-DNA complex as a possible ^{ME}device

In devising emerging fabrication technologies, one may focus on robust *bottom-up* biomolecular assembling which is consistently performed by biosystems. Progress has been made in the synthesis of DNA with specified sequences. Utilizing a motif-based DNA self-assembly, complex 3D structures were synthesized [12, 13]. There are precise binding rules, e.g., adenine A with complementary thymine T and guanine G, with complementary cytosine C. Designs to minimize sequence mismatches is a complex task. The desired assemblies frequently cannot be synthesized due to geometric, thermodynamic and other limits of DNA hybridization [12, 13]. Most importantly, experimental results [21-24] provide evidence that DNA and DNA-derivatives do not exhibit the suitable electronic characteristics even for two-terminal rectifiers, and it is unlikely that suitable device functionality may be achieved. Though the 3D multiinterconnected DNA structures can be synthesized, it seems that it is unreasonable to expect sound DNAcentered electronic devices. The resistor-diode logic is covered in subsection 3.3.3. Although the simple resistor-diode circuits can be theoretically assembled using the DNA motif, this solution may be impractical. The metallization of 3D DNA lattices, which enables electron transport in the metallized segments, cannot be viewed as a sound solution for semiconductor operations. DNA with the appropriate sequence potentially can be used only as a biomolecular-centered wire. The qualitative achievable I-Vcharacteristics for the *admissible* applied voltage for DNA are reported in Figure 14. The magnitude of the applied voltage is bounded due to the thermal stability of the molecule, e.g., $|V| \leq V_{\text{max}}$, and V_{max} is ~1 V depending upon sequence, single versus double stranded, number of base pairs, temperature, functionalization, end-group, etc. For different DNA sequences, the I-V characteristics vary [21], and for the conducting DNA, the characteristics are similar to some organic molecules [2, 4, 14-20]. The asymmetry of the I-V characteristics could be due to the effects related to asymmetric DNA functionalization to the electrodes, contact non-uniformity, or other effects. Three different short (~5.4 nm) double-stranded DNA (dsDNA) sequences, functionalized using short oligonucleotide linkers and

thiol end-groups, were examined in [21]. In particular, Figure 14 documents the experimental results when 15 base-pair single-stranded oligonucleotides

X 3'-(CCGCGCGCCCGCCCG)-5' with a complementary X',

Y 3'-(CCGCGTTTTTGCCCG)-5' with Y',

Z 3'-(GCCTCTCAACTCGTA)-5' with Z',

and

were hybridized to form dsDNA [21]. They were immobilized and functionalized to gold electrodes using $-(CH_2)_3SH$ and $-(CH_2)_6SH$ oligonucleotide linkers to their 3' and 5' ends. An electromigration induced, break-gap test-bed with ~10 nm gap was used to test functionalized dsDNA. There were uncertainties in the testing and characterization, and the number of functionalized dsDNA strands is unknown. Quantitative results, which are of interest, indicate that for the applied voltage, ± 1.2 V, the current in the **X-X**' dsDNA was ± 0.35 nA, while the current in **Y-Y**' dsDNA was ± 0.065 nA. There was no current measured in the random paired **Z-Z**' dsDNA [21]. It is difficult to assume that DNA exhibits a significant potential for electronics with those reported characteristics.



Figure 14. Symmetric and asymmetric I-V characteristics

Templated protein synthesis could be considered to build patterned 3D structures with the desired geometrical topologies. The protein 3D geometry is due to folding of a peptide chain as well as multiple peptide chains. Amino acid bonds determine the folding (alpha helix resulting in helix-loop-helix, beta pleated sheet, random and other conformations). Most proteins evolve through several intermediate states to form stable structures and conformations. The conformation of protein can be reinforced by strong covalent bonds called disulfide bridges. Disulfide bridges form where two cysteine monomers (amino acids with sulfhydryl groups on their side chains) are positioned close by the folding of the protein. Figure 15 illustrates the schematics of the folded protein with hydrogen bonds, ionic bonds and hydrophobic interactions between side chains. These weak bonds and strong covalent (disulfide bridges) bonds could be considered to be similar to 3D biomolecular *circuits*. However, the practicality and feasibility of biomolecular *circuits*, where proteins function as the ^{ME}device or ^Mgates, remain to be examined.



Figure 15. Protein tertiary structure with weak and strong bonds

The existence and superiority of natural biomolecular processing platforms are undisputable facts. However, these biomolecular platforms are profoundly different as compared to synthetic (organic and inorganic) molecular electronics, *solid* and *fluidic*^MICs, and molecular electronics platforms. It is unlikely that the natural biomolecules are utilized (within biomolecular platforms) or can be utilized (within molecular electronics platforms) as electronic elements, components, devices or primitives. It seems that the overall feasibility of using DNA motifs (including the metallized, modified and other solutions) and proteins as electronic devices or circuits does not look promising. In fact, electronic devices ultimately depend on electron transport. Suitable device (or circuit) characteristics and performance are virtually unachievable by DNA or proteins. There is no solid evidence that DNA and proteins can be utilized as ^{ME}devices. In biosystems, the *information coding* (accomplished by the DNA) and the transcription translation mechanism (DNA-RNA-protein), result in the synthesis of biomolecular processing hardware with embedded software. Biomolecules provide unique capabilities to synthesize complex 3D structures. With the attempt to utilize these synthesis abilities, *natural* and modified nitrogenous bases have been studied departing from the DNA-centered theme towards exploring the ^{ME}device-centered solution Different nitrogenous bases. with bioconjugation along and immobilization/quantification/quencher reagents, have been used attempting to ensure sound synthesis and attain the desired electronic characteristics. One may not entirely focus on merely natural biomolecules motifs in devising novel device physics and discovering novel ME devices. Different biomolecules and organic mono- and polycyclic molecules, which have a strong biocentered premise, are proposed and covered in [4] enhancing the *natural* motif. These multi-terminal molecules significantly enlarge the class of molecules to be examined and used to ensure the desired electronic characteristics in order to suit molecular electronics. In particular, functional ^{ME}devices are designed utilizing *input*, *control* and *output* terminals as reported in subsection 3.4.2. Hence, departing from the questionable concept of using DNA and protein as *circuits*, section 3.4.2 introduced ^{ME} devices, which, to some extent, "prototype" the *natural* biomolecules (nitrogenous bases, amino acid R groups, etc.). We propose the alternative solution, e.g., solid molecular electronics.

Hybrid CMOS-technology devices with biomolecules forming the channels are reported in [25-27]. Microelectronic proof-of-concept devices (transistors and sensors) with polymeric guanine (polyG) and other DNA derivatives were designed, analyzed, tested, characterized and evaluated [26, 27]. The polyG FETs were fabricated by slightly modifying the existing CMOS processes. The bio-centered materials employed to form the channel do not result in alternative device physics or departure from general CMOS technology. Though the DNA derivatives have been studied in the CMOS-centered devices, the baseline performance characteristics are found to be impractical. Furthermore, the deposition of DNA and DNA derivatives significantly complicates the overall fabrication and packaging. These DNA FETs can be viewed only as a proof-of-concept demonstration merging the silicon technology with potential biomolecular materials. The FET with polyG $(dG(C_{10})_2)_n$, which is deposited (dropped, with subsequent evaporation) on the silicon oxide (or silicon nitride) between source and drain, is reported in Figure 16 [27]. A CMOS MOSFET is also shown in Figure 16 [4]. For these polyG nFETs, though weakly-controlled current-voltage (I-V) characteristics have been found in the linear region, the saturation region and control features are not adequate. Overall, this solution is found to be not viable. In fact, this solution does not ensure better performance, fabrication advantages or any benefits as compared with the conventional CMOS technology FETs and other devices.



Figure 16. (a) PolyG FET with a channel formed by the adsorbed polyG $(dG(C_{10})_2)_n$; (b) CMOS MOSFET

3.4.2. Multi-Terminal Quantum Effect Molecular Electronic Devices

Quantum-well resonant tunneling diodes and FETs, Schottky-gated resonant tunneling, heterojunction bipolar, resonant tunneling bipolar and other transistors have been introduced to enhance microelectronic device performance. The tunneling barriers are formed using AlAs, AlGaAs, AlInAs, AlSb, GaAs, GaSb, GaAsSb, GaInAs, InP, InAs, InGaP and other composites and spacers with the thickness range from 1 nm to tens of nm. CMOS-technology, high-speed double-heterojunction bipolar transistors provide an ~300 GHz cut-off frequency, ~5 V breakdown voltage and ~1×10⁵ A/cm² current density. The one-dimensional potential energy profile, shown in Figure 17, schematically depicts the first barrier (L_1,L_2), the well region (L_2,L_3) and the second barrier (L_3,L_4) with the quasi-Fermi levels E_{F1} , E_{F23} and E_{F2} . The device physics of these transistors was reported [28], and the electron transport in double-barrier single-quantum-well was straightforwardly examined by applying a self-consistent approach and numerically solving the one- or two-dimensional Schrödinger and Poisson equations [4].



Figure 17. One-dimensional potential energy profile and quasi-Fermi levels in the double-barrier single-well heterojunction transistors

The concept of quantum wells and potential wells/barriers with the width ~ 1 nm, utilized in microelectronic devices, could potentially be implemented using molecules. Publication [29] describes a $D-\sigma-A$ molecular rectifier, with an electron donor moiety (D), bonded to an electron acceptor moiety (A) through an insulating saturated σ bridge. A small reverse current (for negative voltage) and large forward current at the positive voltage result. The nonlinear I-V characteristic results are due to relative arrangements of potentials and HOMO-LUMO-Fermi levels of the two electrodes and the two-terminal molecule leading to electron transport (flow). The length of σ is ~2-10 carbon atoms or their equivalent. Different uni-molecular rectifiers are documented in [2, 14-20]. For example, [17] reports the experimental results for γ -hexadecylquinolinium tricyanoquinodimethanide, **M**, and two thioacetyl derivatives of **M**, (Z)- α -cyano- β -[N-tetradecylthioacetylquinolin-4-ylium)-4-styryl-dicyanomethanide and (Z)- α -cyano- β -[N-hexadecylthioacetylquinolin-4-ylium)-4-styryl-dicyanomethanide. Other rectifiers were studied, for example: (1) 2,6-di[dibutylamino-phenylvinyl]-1-butylpyridinium iodide; (2) dimethylanilino-aza[C₆₀]-fullerene; (3) fullerene-bis-[4-diphenylamino-4"-(N-ethyl-N-2" -ethyl)amino-1,4-diphenyl-1,3-butadiene] malonate. The experimental results for monolayers of the above reported molecules, assembled between Au, Ti, Pt or Al electrodes, exhibit asymmetric I-V characteristics. For example, the I-V characteristic with a hysteresis for a two-terminal Au – monolaver of γ hexadecylquinolinium tricyanoquinodimethanide molecules ($C_{16}H_{33}O-3CNQ$) – Au assembly is illustrated in Figure 18 [4, 17]. The current is very high due to the large area electrodes where the current flows through the millions of molecules.



Figure 18. *I–V* characteristic for a Au–C₁₆H₃₃Q-3CNQ monolayer–Au

Two-terminal molecular diodes and switches are reported in [2, 4, 14-20]. In *solid* ^{ME}devices, quantum effects could be used to ensure the controlled I-V characteristics. For example, quantum interaction, quantum interference, quantum transition, vibration, and Coulomb effect. The device physics, based on these and other phenomena and effects (electron spin, photon-electron-assisted transitions, etc.), must be coherently complemented by the *bottom-up* synthesis of the molecular aggregates which exhibit those phenomena. We considered a 3D-topology with two- and multi-terminal *solid* ^{ME}devices. Figure 19 shows two molecules which must be thiol-functionalized in order to perform the characterization by measuring their I-V and G-V characteristics.



Figure 19. Molecules as potential two-terminal ^{ME} devices (atoms are colored as: H - green, C - cyan, S - yellow and Au - magenta).

(a) 1,4-phenyledithiol molecule and functionalized 1,4-phenyledithiol molecule;

(b) 1,4-phenylenedimethanethiol molecule.

Figure 20 shows a three-terminal 1,3,5-triazine-2,4,6-trithiol molecule. To characterize the derivative 1,3,5-triazinane-2,4,6-trione ($C_3N_3S_3^{-1}$) molecule (TMT), a functionalizable H₃TMT molecule should be used as shown in Figure 20.



Figure 20. 1,3,5-triazine-2,4,6-trithiol molecules, H_3TMT molecule, and functionalized H_3TMT molecule with three Au-S bonds to form three terminals ensuring interconnect

Many organic and inorganic molecules do not meet the desired electronic characteristics due to insufficient controllability, symmetric *I–V* characteristics without desired current saturation region, and thermodynamic sensitivity. Electron transport, tunneling, interactions, charge distributions and other important features are modified by applying potentials to the three terminals. However, the *I–V* characteristics of the functionalized monocyclic H₃TMT, and other symmetric molecules without side groups or asymmetry, may not exhibit the desired behavior. Linear and saturation current regions, robustness are examples. Designing, engineering and analysis of new, functional ^{ME}devices are exceptionally important. We departed from symmetric organic ^{ME}devices by proposing asymmetric multi-terminal carbon-centered ^{ME}devices which contain B, N, O, P, S, I and other doppant atoms. To ensure synthesis feasibility and practicality, these ^{ME}devices are engineered from cyclic molecules and their derivatives.

Consider a multi-terminal *solid* ^{ME}device with controlled electronic characteristics. To specify inputs, controls and outputs, we define the *input*, *output* and *control* terminals. By applying voltage to the *control* terminal, one varies the potential, regulates the charge and electromagnetic field, varies the interactions, and changes the tunneling affecting the electron transport. Hence, the input-output characteristics (I-V and G-V) can be controlled. The monocyclic multi-terminal molecule with side groups is illustrated in Figure 21. Here, X_i denotes the specific atoms (B, C, N, O, Al, Si, P, S, Co, Br and others); R_i denotes the *input/control/output* terminals T_i and/or side groups, $R_i=(T_i, Side Group_i), T_i=(T_k input, T_l control, T_m output).$



Figure 21. Monocyclic molecule as a multi-terminal ^{ME}device

The use of specific atoms and side groups is defined by the device physics, synthesis, aggregability, etc. The aggregation and interconnection of *input/control/output* terminals can be accomplished within the carbon framework. The reported ^{ME}devices possess quantum-effect device physics by exhibiting and utilizing quantum effects and transitions [4]. For example,

- 1. The electron transport is predefined or affected by X_i and side groups;
- 2. Atomic structures of side groups can exhibit transitions or interactions under the external electromagnetic excitations and thermal gradient;
- 3. Side groups can be utilized as electron *donating* and electron *withdrawing* substituent groups, as well as interacting or interconnect groups.

The ^MAND and ^MNAND gates are shown in Figure 22 utilizing multi-terminal ^{ME}devices to form ^Mgates. Figure 22 illustrates the overlapping molecular orbitals for cyclic molecules used to implement these ^Mgates.



Figure 22.^MAND and ^MNAND gates comprised from cyclic molecules

The ^Mgates, designed using cyclic molecules as ^{ME}devices, are depicted in Figure 23.



^MOR ^MMUX Figure 23. Molecular gates: ^Minverter, ^MAND, ^MNAND, ^MOR, ^MNOR, ^MXOR and ^MMUX which can be utilized in the implementation of ^Nhypercells

We considered a three-terminal ^{ME} device with the *input*, *control* and *output* terminals as shown in Figures 21 and 24. The device physics of the proposed ^{ME} device is based on the quantum interaction and controlled electron transport. The applied $V_{control}(t)$ changes the charge distribution $\rho(t,\mathbf{r})$ and $E_E(t,\mathbf{r})$ affecting the electron flow. This ^{ME} device operates in the controlled electron-exchangeable environment due to quantum effects. Controlled super-fast potential-assisted electron transport can be achieved [4]. Electron-exchangeable environmental interactions qualitatively and quantitatively modify the device behavior and its characteristics. Consider electron transport in the time- and spatial-varying metastable potentials $\Pi(t,\mathbf{r})$. From the quantum theory viewpoint, the changes in the Hamiltonian result in changes of tunneling T(E) and quantum transitions due to variations of $\rho(t,\mathbf{r})$, $E_E(t,\mathbf{r})$ and $\Pi(t,\mathbf{r})$. The device

controllability is ensured by varying $V_{\text{control}}(t)$ that affects the device switching, I-V and other characteristics.



Figure 24. Three-terminal ^{ME}device comprised from a cyclic molecule with a carbon interconnecting framework

We performed high-fidelity modeling and data-intensive analysis for the studied ^{ME}device. For heterojunction microelectronic devices, one usually solves the one-dimensional Schrödinger and Poisson equations applying the Fermi-Dirac distribution function. In contrast, for the devised ^{ME}devices, a 3D problem arises which cannot be simplified. Furthermore, the distribution functions and statistical mechanics postulates may not be straightforwardly applied [4]. For the studied cyclic molecule which forms an interconnected ^{ME}device, we consider 9 atoms with motionless protons with charges q_i .

The radial Coulomb potentials are
$$\prod_{i}(r) = -\frac{Z_{eff i}q_{i}^{2}}{4\pi\varepsilon_{0}r}$$
. For carbon $Z_{eff C}=3.14$.

Using the spherical coordinate system, the Schrödinger equation

$$-\frac{\hbar^2}{2m}\left[\frac{1}{r^2}\frac{\partial}{\partial r}\left(r^2\frac{\partial\Psi}{\partial r}\right) + \frac{1}{r^2\sin\theta}\frac{\partial}{\partial\theta}\left(\sin\theta\frac{\partial\Psi}{\partial\theta}\right) + \frac{1}{r^2\sin^2\theta}\frac{\partial^2\Psi}{\partial\phi^2}\right] + \Pi(r,\theta,\phi)\Psi(r,\theta,\phi) = E\Psi(r,\theta,\phi)$$

should be solved. It is impractical to find the analytic solution by using the separation of variables concept. Instead, the Schrödinger and Poisson equations were discretized in order to numerically solve these differential equations. The magnitude of the time-varying potential applied to the *control* terminal is bounded due to the thermal stability of the molecule, e.g., $|V_{\text{control}}| \leq V_{\text{control}}| \leq 0.2 \text{ V}$. The charge distribution is of particular interest. Figure 25 documents a three-dimensional charge distribution in the molecule if $V_{\text{control}} = 0.1 \text{ V}$ and $V_{\text{control}} = 0.2 \text{ V}$. The total molecular charge distribution was found by summing the individual orbital densities.



Figure 25. Charge distribution $\rho(\mathbf{r})$

The Schrödinger and Poisson equations were solved using a self-consistent algorithm in order to verify the soundness of the device physics and examine the baseline performance characteristics. To obtain the current density **j** and current in the ^{ME}device, the velocity and momentum of the electrons were obtained by making use of $\langle p \rangle = \int_{0}^{\infty} \Psi^{*}(t,\mathbf{r}) \left(-i\hbar \frac{\partial}{\partial \mathbf{r}}\right) \Psi(t,\mathbf{r}) d\mathbf{r}$. The wave function $\Psi(t,\mathbf{r})$ was derived for

distinct values of V_{control} . The *I*–*V* characteristics of the studied ^{ME}device for two different control currents (0.1 and 0.2 nA) are given in Figure 26. The results documented imply that the proposed ^{ME}device may be

effectively used as a multiple-valued or symbolic molecular primitives in order to design enabling multiple-valued or symbolic logic and memory.



Figure 26. Multiple-valued I-V characteristics

The traversal time of electron tunneling is derived from the expression $\tau(E) = \int_{r_0}^{r_f} \sqrt{\frac{m}{2[\Pi(\mathbf{r}) - E]}} d\mathbf{r}$. It is found that τ varies from 2.4×10⁻¹⁵ to 5×10⁻¹⁵ sec [4]. Hence, the proposed ^{ME}device ensures super-fast

is found that τ varies from 2.4×10 ° to 5×10 ° sec [4]. Hence, the proposed endevice ensures super-fast switching.

The reported monocyclic molecule can be used as a six-terminal ^{ME}device as illustrated in Figure 27. The proposed carbon-centered molecular hardware solution, in general,

- 1. Ensures a sound *bottom-up* synthesis at the device, gate and module levels;
- 2. Guarantees aggregate ability to form complex ^MICs;
- 3. Results in the experimentally characterize able ^{ME} devices and ^M gates.



Figure 27. Six-terminal ^{ME}devices

The use of the side groups R_i , shown in Figure 27, ensures the variations of the energy barriers and well potential surfaces $\Pi(t,\mathbf{r})$. This results in controlled electron transport, as well as controlled quantum transitions and interactions. As reported, the studied ^{ME}devices can be utilized in combinational and memory ^MICs. In addition, those devices can be used as routers. Hence, one achieves a reconfigurable networking and processing-and-memory solution. We conclude that a reconfigurable neuromorphological architecture can be implemented.

3.5. PROOF-OF-CONCEPT CAD AND SOFTWARE DEVELOPMENTS

3.5.1. CAD and Software Developments for SLSI Design

Fully featured technology-dependent CAD for SLSI design is a significant task that was not within the scope of this project. The representative CAD tools and software solutions were developed in order to demonstrate design feasibility. In particular, approaching SLSI design tasks, we developed a Linear Decision Diagram (LWDD) Package and Windows-Based 3D ICs Interactive Toolbox (WindowIT) using C and OpenGL. *Microsystems and Nanotechnologies* has been engaging in the integration of both packages. Compatibility with hardware description languages is important. To be compatible with conventional logical programming tools, three netlist formats (Electronic Data Interchange Format - EDIF, International Symposium on Circuits and Systems - ISCAS, and Berkeley Logic Interchange - BLIF) were used and embedded in the LWDD Package. The methods reported in section 3.3 were used in the software development. Using the proof-of-concept CAD tools, we can examine baseline characteristics and prove the efficiency, robustness, feasibility and other significant advantages of the proposed 3D³ technology which focuses on the SLSI design. A more complete analysis of SLSI-designed ICs could be performed when a fully-featured CAD environment for molecular electronics technology is developed.

The representative components of the developed CAD prototype (LWDD Package and WindowIT), allow one to carry-out the design of ICs. The software, developed by *Microsystems and Nanotechnologies*, was successfully tested and verified. The LWDD Package features:

- 1. New sound design methods for 3D ICs and ^MICs;
- 2. Synthesis and partitioning linear decision diagrams for given functions or circuits;
- 3. Spectral representation of logic functions;
- 4. Circuit verification;
- 5. Compact format for rapid-prototyping;
- 6. Compressed representation of complex logic networks.

Results in design and visualization of 3D ICs are reported in Figure 28.a, displaying the Command Windows data for the LWDD Package which is envisioned to be a part of the SLSI CAD software. Figure 28.b shows the results of the design for a c17 circuit in 3D.



(b) Figure 28. (a) Command Window of the LWDD Package to perform design of ICs in 3D; (b) Design of c17 circuit, and c17 implementation using ^MNAND gates.

The results of the design for an 8-bit ALU, e.g., well-known c880, are displayed in Figure 29.

🔤 C:\SLSI3DMICs\LDDPackage.exe	- 🗆 🗙
Level 15	
665gat -1*2^0+1*2^2 //for the input that is a fan-out of 665gat 815gat -1*2^0+1*2^2-1*2^23 //for the input that is a fan-out of 815gat	
673gat -1*2^4+1*2^6 //for the input that is a fan-out of 673gat	
819 gat $-1*2^4+1*2^6$ //for the input that is a fan-out of 819 gat	
682 gat $-1*2^{-}8+1*2^{-}10$ //for the input that is a fan-out of 682 gat 822 gat $-1*2^{-}8+1*2^{-}10$ //for the input that is a fan-out of 822 gat	
219gat +1*2^12 //for the input that is a fan-out of 219gat	
825 gat $+1*2^{12}$ //for the input that is a fan-out of 825 gat	
826gat $-1*2$ 14 //for the input that is a fan-out of 826gat 1929gat $-1*2^{-14}$ //for the input that is a fan-out of 227gat	
704 yat $-1 \times 2^{-1}4$ //for the input that is a fan-out of 704 yat	
827gat -1*2^17 //for the input that is a fan-out of 827gat	
701gat -1+2 17 //for the input that is a fan-out of 710gat	
527 gat $-1*2^17$ //for the input that is a fan-out of 527 gat	
828 gat $-1*2^20$ //for the input that is a fan-out of 828 gat	
735 gat $-1*2/20$ //for the input that is a fan-out of 735 gat $-1*2/20$ //for the input that is a fan-out of 721 gat	
528 gat -1×2^20 //for the input that is a fan-out of 528 gat	
593gat -1*2^23 //for the input that is a fan-out of 593gat	
1966 +2*2 9+2*2 4+2*2 8+6*2 14+7*2 17+7*2 29+3*2 23 //10P the fPee term: node	Inal
Level 16	
830gat $-1*2^{0}$ //for the input that is a fan-out of 830gat	
831 gat $-1*2$ 9 //for the input that is a fan-out of 831 gat 832 gat $-1*2$ //for the input that is a fan-out of 832 gat	
333 gat -1×2^2 //for the input that is a fan-out of 833 gat	
834gat $-1*2^4$ //for the input that is a fan-out of 834gat	
835 gat $-1*2^{-2}4$ //for the input that is a fan-out of 835 gat $-3*2^{-6}$ //for the input that is a fan-out of 33 gat	
336 gat $-1 \times 2^{\circ}6$ //for the input that is a fan-out of 836 gat	
590gat $-1*2^8$ //for the input that is a fan-out of 590gat	
841gat +1*2'8 //for the input that is a fan-out of 841gat $\frac{1}{2}$ $\frac{1}{2}$	
Level 17	
219gat $\pm1*2^0\pm1*2^2\pm1*2^4$	
842 gat $\pm 1 \times 2$ 0 //for the input that is a fan-out of 842 gat 842 gat $\pm 1 \times 2^{\circ}$ 2 //for the input that is a fan-out of 842 gat	
844gat +1×2^4 //for the input that is a fan-out of 844gat	
845 gat $-1*2^{\circ}6$ //for the input that is a fan-out of 845 gat	
$772gat -1\pi2$ b //for the input that is a fan-out of $772gat$	
free +6×2^6 //for the free terminal node	
Level 18	
$41/gat -1 \star 20$ //for the input that is a fan-out of $41/gat$	
332 gat -1×2^2 //for the input that is a fan-out of 332 gat	
852 \overline{g} at $-1*2^2$ //for the input that is a fan-out of 852 \overline{g} at	
333gat -1*2.4 //for the input that is a fan-out of $333gat853gat -1*2^4 //for the input that is a fan-out of 853gat$	
free +2*2^0+2*2^2+2*2^4 //for the free terminal node	
Level 19	
859gat -1*270 //for the input that is a fan-out of 859gat 769gat -1*270 //for the input that is a fan-out of 769gat	
669gat -1*2^0 //for the input that is a fan-out of 669gat	
860gat $-1*2^3$ //for the input that is a fan-out of 860gat	
770gat -1*273 //for the input that is a fan-out of 770gat 679gat -1*273 //for the input that is a fan-out of 679gat	
861gat -1*2^6 //for the input that is a fan-out of 861gat	
771gat -1*2^6 //for the input that is a fan-out of 771gat	
free th*2^0+6*2^3+6*2^6 //for the free terminal node	
>> ri ICs/c880.isc	
>> Ina	
77.01a Time: 0.047	
>> pns	
Inputs: 60	
Gates: 294	
Levels: 19	

Figure 29. Design of an 8-bit ALU (c880)

The application of the WindowIT environment to perform the design and implementation of molecular primitives is documented in Figure 30.a and 30.b. In particular, ^MICs were designed and implemented as aggregated hypercubes and ^Nhypercells, respectively. Figure 30.a shows a ^MNAND gate design and its implementation. A generic 3D hypercube, configured into a two-to-one molecular multiplexer (^MMUX), is depicted in Figure 30.b. Molecular multiplexers and other ^Mgates (^Minverter, ^MAND, ^MNAND, ^MOR, ^MNOR and ^MXOR), designed by the *Microsystems and Nanotechnologies* team using cyclic carbon-based molecules, can be visualized by the software tools developed, see Figure 30.a.



Figure 30. Design of 3D^MICs using interactive WindowIT software that performs integration, aggregation and visualization

3.5.2. Three-Dimensional Design of ICs and Proof-of-Concept ALU

As reported in sections 3.5.1, *Microsystems and Nanotechnologies* started the development of the CAD tools and other software to verify and demonstrate the SLSI design concept, $3D^3$ technology, methods developed and innovations proposed. The proposed design of ^MICs in 3D was illustrated and verified using ICs designed applying the VLSI and ULSI tools. A series of numerical studies were conducted to accomplish the software-supported logic design for proof-of-concept ICs. The size of LWDDs generated by the developed software was compared with the best results obtained by using the Decision Diagram Packages, developed by the University of Colorado and Darmstadt University of Technology, for 2D VLSI design. For the concept reported, the software and algorithms were tested and validated. The number of nodes, number of levels and CPU time (in seconds) required to design decision diagrams for 3D ICs are reported in Table 1. The logic designs for a 9-bit ALU (c5315) and multiplier (c6288), for which a classical decision diagram may not be effectively used, were successfully performed.

Circuit I/O	BDD WDD	LWDD (EDIF)	LWDD (ISCAS'85)
	#N	# L # N CPU Time	#L #N CPU Time
C432 36/7	1064 1209	21 455 <0.01	17 336 <0.001
8-bit ALU	4053 4048	35 604 <0.01	24 605 <0.1
C880 60/26			
c2670 233/140	1850 3939	40 1374 <0.1	32 2026 <0.1
9-bit ALU			
c5315 178/123	1719 2504	68 3192 <0.3	49 4156 <0.4
Multiplier			
c6288 32/32		124 4320 <0.2	124 4318 <0.5

Table 1. Design summary (number of nodes, levels and CPU time) for BDD, WDD and LWDD

In the design we assumed: (1) Feedforward neural network without feedback; (2) Threshold ^Mgates were used; (3) Aggregated networked 3D ⁸hypercells were comprised from ^Mgates; (4) Multilevel combinational circuits were used over the library of NAND, NOR and EXOR ^Mgates.

Numerical studies (design) were conducted for different circuits. The results are reported in Tables 1 and 2 for the representative circuits (for which the conventional methods result in some inconsistencies or drawbacks). We examine volumistic size, topological parameters, performance and validate the design. The space size is given by *X*, *Y* and *Z* that result in the volumistic (*V*) quantity $V=X\times Y\times Z$. The topological characteristics were evaluated using the total number of terminals (N_T) and intermediate (N_I) nodes. A 3D 9-bit ALU (c5315) with 178 inputs and 123 outputs was implemented using 1413 ^Mgates, while a c6288 multiplier (32 inputs and 32 outputs) has 2327 ^Mgates. The number of incompletely specified hypercubes and ⁸hypercells was minimized. The hypercubes in the *i*th layer were connected to the corresponding cubes in the (*i*–1)th and (*i*+1)th layers. The obtained 3D topology had $X\times Y\times Z$ hypercubes. The number of terminal nodes and intermediate nodes were 3750 and 2813 for a 9-bit ALU, while, for a multiplier, we had 9248 and 6916 nodes. To combine all layers, more than 10,000 connections were generated. The design in 3D was performed within 0.4 seconds. Other metrics to evaluate the designed 3D ICs were used. In addition to conventional parameters (diameter, dilation cost, expansion, load, etc.), we used the number of variables in the logic function described by hypercubes, number of links, fan-out of the intermediate nodes, statistics, etc.

Circuit I/O		Spac	e Size	;	Nodes a	and Conr	nections	
	#G	#X	#Y	#Z	$\#N_T$	$\# N_I$	CPU Time	
c432 36/7	126	66	64	66	2022	1896	< 0.01	
8-bit ALU								
c880 60/26	294	70	72	70	612	482	< 0.1	
c2670 233/140	828	82	80	78	3594	2766	<0.1	
9-bit ALU								
c5315 178/123	1413	138	132	126	3750	2813	<0.4	
Multiplier								
c6288 32/32	2327	248	248	244	9246	6916	< 0.5	

Table 2. Numerical results for 3D ICs

Comparison of 2D and 3D designs for a 9-bit ALU. The high-level ALU model is documented in Figure 31. The studied ALU performs arithmetic and logic operations simultaneously on two 9-bit input data words, and computes the parity of the results. Conventional 2D logic design of a 9-bit ALU (c5315 circuit) with 178 inputs and 123 outputs results in 2406 gates. In contrast, the proposed design, carried-

out by the LWDD Package, leads to 1413 ^Mgates that are networked and aggregated in 3D. The results of the design for the studied 9-bit ALU are displayed in Figure 32.



Figure 31. High-level model for a 9-bit ALU (c5315 circuit)

ex C:V	SLS13DMICs\LDDPackage.exe		_ 🗆 🗙
Level	28	6	▲ 0.000 ▲
839 840	+1*2^0 //for the input that is +1*2^0 //for the input that is	s a fan-out s a fan-out	of 839 of 840
841	+1*2^0 //for the input that is	s a fan-out	of 841
842	$+1 \times 2^{0}$ //for the input that is	s a fan-out	of 842
879	$+1*2^3$ //for the input that is	s a fan-out	of 879
880	+1*2^3 //for the input that is	s a fan-out	of 880
881	$+1*2^3$ //for the input that is	s a fan-out	of 881 of 3648
3649	+1*2^6 //for the input that is	s a fan-out	of 3649
3651	+1*2^8 //for the input that is	s a fan-out	of 3651
3652 free	+1*2"8 //for the input that is +3*2^0+3*2^3+1*2^6+1*2^8	s a fan-out //for the	ot 3652 free terminal node
Level	29		
3657	+1*2^0+1*2^4 //for the input	t that is a	fan-out of 3657
2	102 0 102 2 102 1 102 0	//IOP CHE	input that is a fail out of 407
3658	+1*2^2+1*2^6 //for the input	t that is a	fan-out of 3658
free Leuel	+1*20+1*22+1*24+1*2P	//for the	free terminal node
3636	+1*2^0 //for the input that is	s a fan-out	of 3636
3637	$+1*2^0$ //for the input that is	s a fan-out	of 3637
3640	+1×2 2 //for the input that is	s a ran-out s a fan-out	of 3640
3642	+1*2^4 //for the input that is	s a fan-out	of 3642
3643	$+1*2^{4}$ //for the input that is	s a fan-out	of 3643
3646	$+1\times2^{6}$ //for the input that is	s a fan-out	of 3646
free	+1*2^0+1*2^2+1*2^4+1*2^6	//for the	free terminal node
16761 1676	31 +1*2^0+1*2^6 //fow the input	that is a	fap-out of 3656
4088	-1*2^0+1*2^3 //for the input	t that is a	fan-out of 4088
4087	-1*2^0-1*2^3 //for the input	t that is a	fan-out of 4087
3655 4089	-1*2^6+1*2^9 //for the input	t that is a t that is a	fan-out of 3655 fan-out of 4089
4090	-1*2^6-1*2^9 //for the input	t that is a	fan-out of 4090
3654	+1*2^12+1*2^18 //for the input	t that is a	fan-out of 3654
1689 1690	-1*2^12+1*2^15 //for the input -1*2^12-1*2^15 //for the input	t that is a t that is a	fan-out of 1689 fan-out of 1690
3653	+1*2^15+1*2^21 //for the input	t that is a	fan-out of 3653
1691	$-1*2^{18+1}*2^{21}$ //for the input	t that is a	fan-out of 1691
free	+3*2^0+2*2^3+3*2^6+2*2^9+3*2^1	2+2×2^15+3×	$2^{18+2}\times2^{21}$ //for the free t
ermin	al node		
1657	$\frac{32}{+1*2^{0}}$ //for the input that is	s a fan-out	of 1657
1659	+1*2^0 //for the input that is	s a fan-out	of 1659
1660	$+1*2^0$ //for the input that is	s a fan-out	of 1660
2328	$+1 \times 2^{3}$ //for the input that is	s a fan-out s a fan-out	of 2328
2330	+1*2^3 //for the input that is	s a fan-out	of 2330
2331	+1*2^3 //for the input that is	s a fan-out	of 2331
763	+1*2^6 //for the input that is	s a fan-out	of 763
764	+1*2^6 //for the input that is	s a fan-out	of 764
765	+1+2 6 //for the input that is	s a fan-out s a fan-out	of 766
803	+1*2^9 //for the input that is	s a fan-out	of 803
804	$+1*2^9$ //for the input that is	s a fan-out	of 804
805	$+1*2^9$ //for the input that is $+1*2^9$ //for the input that is	s a fan-out s a fan-out	of 805
free	+3+2^0+3+2^3+3+2^6+3+2^9	//for the	free terminal node
Level	33 +1*2^0 //for the input that i	a fan-out	of 1662
137	+1*2*0+1*2*2 //for the input	t that is a	fan-out of 137
2333	+1*2^2 //for the input that is	s a fan-out	of 2333
free \rightarrow wi	//for the free terminal ICs/c5315 isc	1 node	
\rightarrow \ln	a		
>> b1	a		
>> nn	0.30 2		
Input	s: 178		
Output	ts: 123		
Gates Level	• 1413 s: 33		
>>			•

Figure 32. Design of a 9-bit ALU

4. CONCLUSIONS

As documented in this report, *Microsystems and Nanotechnologies* has successfully completed all Tasks outlined in the Statement of Work. Innovative developments in devising, design and analysis of novel molecular computing and processing platforms were carried-out and reported. Enabling hardware and software solutions were proposed, which ultimately resulted in the development of $3D^3$ technology. Molecular electronics and ^MICs, were examined. These innovations are leading to super-highperformance computing uniquely utilizing proposed 3D-topology ^{ME}devices, ^Nhypercells, fused processing-and-memory organization, reconfigurable ^{3D} networking-and-processing neuromorphological architecture and SLSI design. A wide spectrum of fundamental, applied and experimental issues, related to the design, device physics, functionality, performance and capabilities were studied and are under further development. An innovative concept in SLSI design of ^MICs was reported. This concept was verified and demonstrated for various circuits demonstrating the applicability the design method reported and the effectiveness of representative CAD tools. Though a great number of problems remain to be addressed and solved, it was demonstrated that the proposed molecular computing platforms provide overall supremacy ensuring high-performance processing. We focused on development of a feasible, practical, affordable and superior 3D³ technology for massive parallel distributed computing and processing for Air Force systems.

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LIST OF ABBREVIATIONS AND ACRONYMS

2D	- Two-dimensional
3D	- Three-dimensional
ALU	- Arithmetic logic unit
BJT	- Bipolar junction transistor
CAD	- Computer-aided-design
CMOS	- Complimentary metal-oxide semiconductor
DD	- Decision diagram
DNA	-Deoxyribonucleic acid
dsDNA	- Double stranded DNA
FET	- Field-effect transistor
G - V	- Conductance-voltage characteristic
НОМО	- Highest occupied molecular orbital
[*] hypercell	- Neuronal hypercell
IC	- Integrated circuit
MIC	- Molecular integrated circuit
MEdevice	- Molecular Electronics device
I–V	- Current-voltage characteristic
^M gate	- Molecular gate
^M MUX	- Molecular Multiplexers
LWDD	- Linear decision diagrams
LP	- Linear arithmetic polynomial
LUMO	- Lowest unoccupied molecular orbital
LWDD	- Linear word-level decision diagrams

SLSI	- Super-large-scale integration
SOW	- Statement of Work
SRAM	- Static random access memory
VLSI	- Very-large-scale integration
ULSI	- Ultra-large-scale integration